

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Forward Voltage (Note 2) $I_F=10mA$	V_F	0.9	V
Power Dissipation(Note 1)	P_D	200	mW
Typical Thermal Resistance Junction to Ambient(Note 1)	R_{JA}	625	/W
Junction and Storage Temperature Range	T_J, T_{stg}	-65 150	

/ Electrical Characteristics(Ta=25)

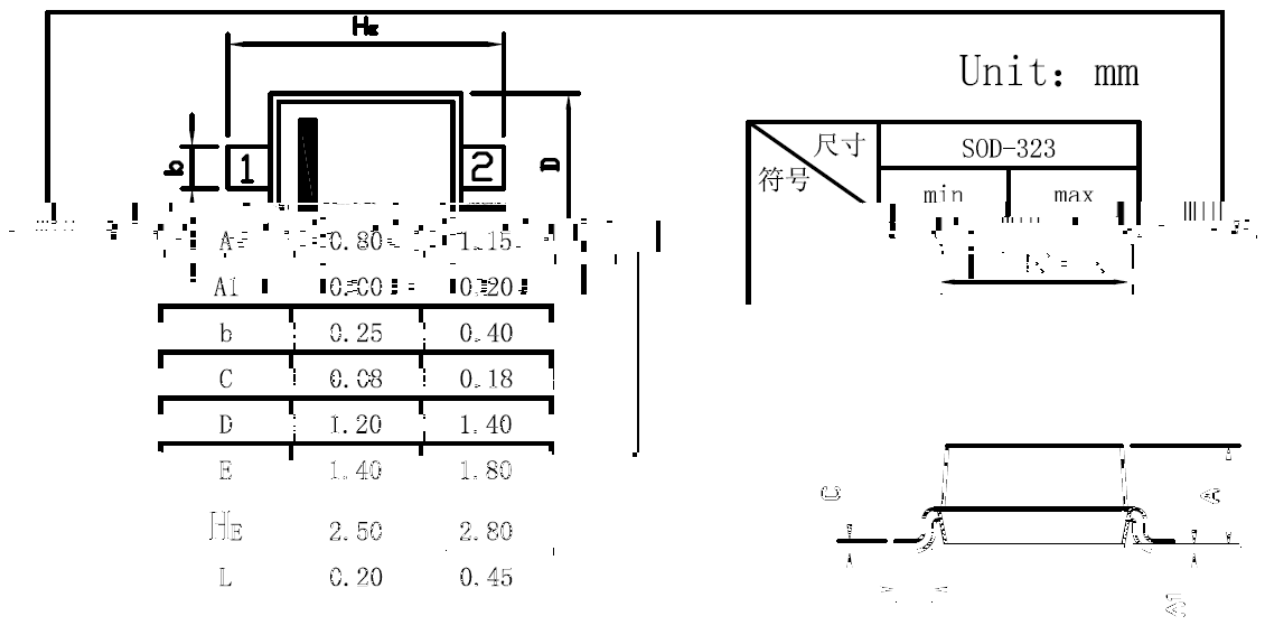
Type Number	Marking Code	Zener Voltage Range (Note 2)				Maximum Zener Impedance (Note 3)			Maximum Reverse Current	
		$V_Z @ I_{ZT}$			I_{ZT}	$Z_{ZT} @ I_{ZT}$	$Z_{ZK} @ I_{ZK}$	I_{ZK}	I_R	@ V_R
		Nom (V)	Min (V)	Max (V)	mA				A	V
BRBZT52B2V4SQ	Q0Z	2.4	2.35	2.45	5	94	564	1	45	1
BRBZT52B2V7SQ	Q1Z	2.7	2.65	2.75	5	94	564	1	18	1
BRBZT52B3V0SQ	Q2Z	3.0	2.94	3.06	5	89	564	1	9	1
BRBZT52B3V3SQ	Q3Z	3.3	3.23	3.37	5	89	564	1	4.5	1
BRBZT52B3V6SQ	Q4Z	3.6	3.53	3.67	5	84	564	1	4.5	1
BRBZT52B3V9SQ	Q5Z	3.9	3.82	3.96	5	84	564	1	2.7	1
BRBZT52B4V3SQ	Q6Z	4.3	4.21	4.39	5	84	564	1	2.7	1
BRBZT52B4V7SQ	Q7Z	4.7	4.61	4.79	5	75	564	1	2.7	2
BRBZT52B5V1SQ	Q8Z	5.1	5.00	5.20	5	56	470	1	1.8	2
BRBZT52B5V6SQ	Q9Z	5.6	5.49	5.71	5	27	451	1	0.9	2
BRBZT52B6V2SQ	QAZ	6.2	6.08	6.32	5	9	376	1	2.7	4
BRBZT52B6V8SQ	QBZ	6.8	6.66	6.94	5	14	141	1	1.8	4
BRBZT52B7V5SQ	QCZ	7.5	7.35	7.65	5	14	75	1	0.9	5
BRBZT52B8V2SQ	QDZ	8.2	8.04	8.36	5	14	75	1	0.63	5
BRBZT52B9V1SQ	QEZ	9.1	8.92	9.28	5	14	94	1	0.45	6
BRBZT52B10SQ	QFZ	10	9.80	10.20	5	18	141	1	0.18	7
BRBZT52B11SQ	QGZ	11	10.78	11.22	5	18	141	1	0.09	8



Notes:

1. Device mounted on ceramic PCB; 7.6mm x 9.4mm x 0.87mm with pad areas 25mm².
2. Short duration test pulse used to minimize self-heating effect.
3. $f = 1\text{kHz}$.

/ Package Dimensions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)

- 備 註
- 1 預熱 150 ℃~200 ℃ 時間 60 ~120sec;

2 峰值溫度 255 ± 5 ℃ 時間 5 ~10 sec;

3 冷卻速度 2 ~10 ℃ /sec.

Note:

1.Preheating:150~200 ℃ , Time:60~120sec.

2.Peak Temp.:255 ± 5 ℃ , Duration:5 ~10 sec.

3. Cooling Speed: 2~10 ℃ /sec.